

Abstract of Disclosure

A memory includes a first diffusion layer, a second diffusion layer, a first polysilicon layer, a second polysilicon layer, a first resistive memory element and a second resistive memory element.

- 5 The first diffusion layer and the second diffusion layer formed along a first direction. The first polysilicon layer formed along a second direction and formed to at least partially overlap with the first diffusion layer and second diffusion layer, such that the first direction is substantially perpendicular to the second direction. The second polysilicon layer formed along the second direction and formed to at least partially overlap with the first diffusion layer and the second
- 10 diffusion layer. The first resistive memory element is formed at least partially overlaps the first diffusion layer and between the first and second polysilicon layers. The second resistive memory element formed at least partially overlaps the second diffusion layer and between the first and second polysilicon layers.

15 FIG. 4